RS1AF~ RS1MF

RECTIFIER DIODE

1A SURFACE MOUNT FAST RECOVERY RECTIFIER

FEATURES

The RS1AF~RS1MF are available in SMAF Package

- Glass Passivated Chip Junction
- Fast Recovery Time for High Efficiency
- Surge Overload Rating to 25A Peak
- Ideally Suited for Automated Assembly

MECHANICAL DATA

· Case: SMAF

 Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 27mg / 0.00086oz

ORDERING INFORMATION

Package Type	Part Number			
SMAF	RS1AF			
	RS1BF			
	RS1DF			
	RS1GF			
	RS1JF			
	RS1KF			
	RS1MF			
SPQ	3,000pcs/Reel			
AiT provides all RoHS Compliant Products				

PIN DESCRIPTION





SMAF

- 1 Cathode
- 2 Anode

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified.

Parameter	Symbols	RS1AF	RS1BF	RS1DF	RS1GF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	V
Maximum Average Forward Rectified Current at $T_A = 65 ^{\circ}\text{C}$	I _{F(AV)}	1			А	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	25			А	
Maximum Instantaneous Forward Voltage at 1 A	VF		1	.3		V
Maximum DC Reverse Current T _A = 25 °C at Rated DC Blocking Voltage T _A =125 °C	I _R	5 100				μA
Maximum Reverse Recovery Time*	t _{rr}		1	50		ns
Typical Junction Capacitance **	Cj		1	15		pF
Operating and Storage Temperature Range	T_j , T_{stg}	-55 ~ +150			°C	
Parameter	Symbols	RS1JF	RS	S1KF	RS1MF	Units
Parameter Maximum Repetitive Peak Reverse Voltage	Symbols V _{RRM}	RS1JF 600		800	RS1MF 1000	Units V
	-		8			
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	600	5	300	1000	V
Maximum Repetitive Peak Reverse Voltage Maximum RMS voltage	V _{RRM} V _{RMS}	600 420	5 8	800 860	1000 700	V
Maximum Repetitive Peak Reverse Voltage Maximum RMS voltage Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at	V _{RRM} V _{RMS} V _{DC}	600 420	5 8	300 560 300	1000 700	V V V
Maximum Repetitive Peak Reverse Voltage Maximum RMS voltage Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _A = 65 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	VRRM VRMS VDC IF(AV)	600 420	8 8	800 860 800	1000 700	V V V
Maximum Repetitive Peak Reverse Voltage Maximum RMS voltage Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _A = 65 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	VRRM VRMS VDC IF(AV)	600 420	2	300 360 300 1	1000 700	V V V A
Maximum Repetitive Peak Reverse Voltage Maximum RMS voltage Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _A = 65 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method) Maximum Instantaneous Forward Voltage at 1 A Maximum DC Reverse Current T _A = 25 °C	VRRM VRMS VDC IF(AV) IFSM	600 420	2	300 360 300 11 25 .3	1000 700	V V V A
Maximum Repetitive Peak Reverse Voltage Maximum RMS voltage Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at TA = 65 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method) Maximum Instantaneous Forward Voltage at 1 A Maximum DC Reverse Current TA = 25 °C at Rated DC Blocking Voltage TA =125 °C	VRRM VRMS VDC IF(AV) IFSM VF	600 420 600	2 2 1	300 360 300 1 25 .3 5 00	1000 700	V V V A A V

Measured with I_F = 0.5 A, I_R = 1 A, I_{rr} = 0.25 A

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

^{**} Measured at 1MHz and applied reverse voltage of 4V D.C.

TYPICAL CHARACTERISTICS

Fig 1. Forward Current Derating Curve

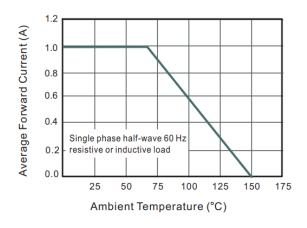


Fig 2. Typical Reverse Characteristics

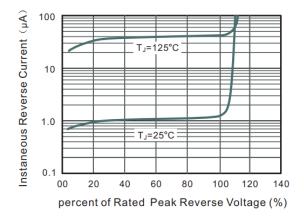


Fig 3. Typical Instantaneous Forward Characteristics

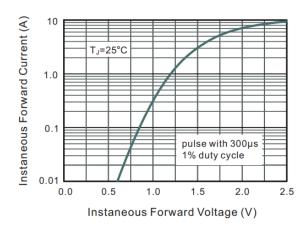


Fig 4. Typical Junction Capacitance

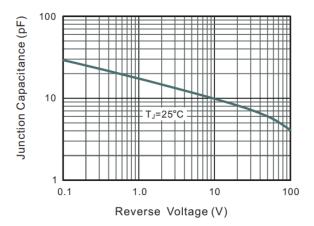
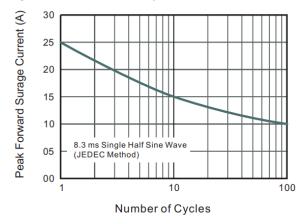


Fig 5. Maximum Non-Repetitive Peak Forward Surge Current

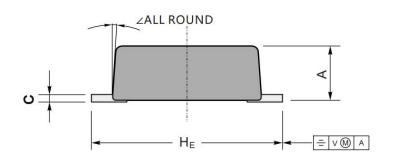


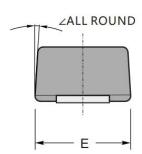
RECTIFIER DIODE

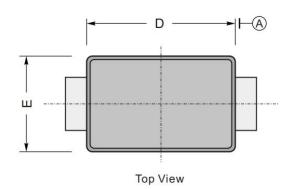
1A SURFACE MOUNT FAST RECOVERY RECTIFIER

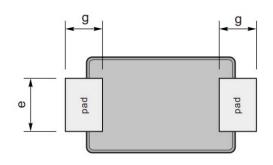
PACKAGE INFORMATION

Dimension in SMAF (Unit: mm)

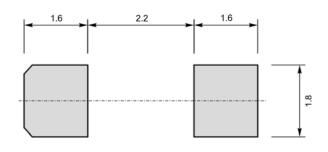








Bottom View



RECOMMENDED LAND PATTERN

Symbol	Min	Max	
А	0.9	1.1	
С	0.12	0.20	
D	3.3	3.7	
E	2.4	2.7	
е	1.3	1.6	
g	0.8	1.2	
HE	4.4	4.9	
∠	7°		

RS1AF~ RS1MF

RECTIFIER DIODE

1A SURFACE MOUNT FAST RECOVERY RECTIFIER

IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc. integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or server property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.